

SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET MCH3479 — General-Purpose Switching Device **Applications**

Features

- ON-resistance $R_{DS}(on)1=49m\Omega$ (typ.)
- 1.8V drive
- · Halogen free compliance
- · Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

0.15

.0 to 0.02

1 : Gate 2 : Source

3 : Drain

SANYO : MCPH3

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		3.5	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	14	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

MCH3479-TL-H

Package Dimensions

unit : mm (typ) 7019A-003

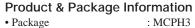
2.1

0.25

70.0

0.65

0.3



: MCPH3

: SC-70, SOT-323

• Minimum Packing Quantity : 3,000 pcs./reel

Packing Type : TL

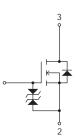
• JEITA, JEDEC







Electrical Connection



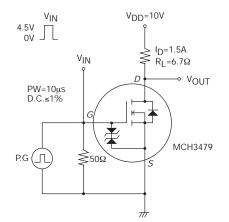
SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

60612 TKIM/81110PE TK IM TC-00002457 No. A1813-1/7

Electrical Characteristics at Ta=25°C

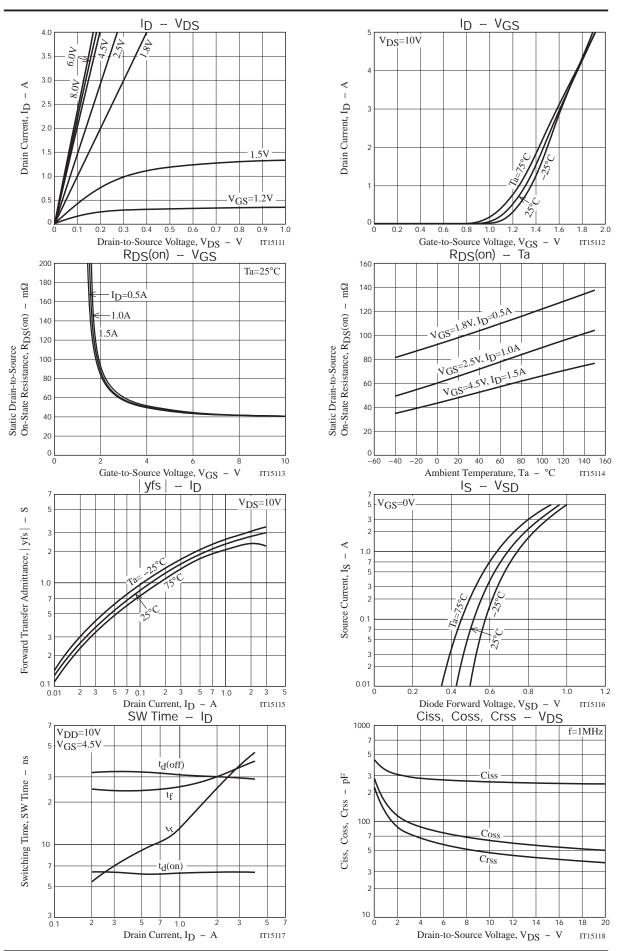
Devenator	Cumple of	Quere s'Allere e		1.114			
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A		2.8		S	
	R _{DS} (on)1	ID=1.5A, VGS=4.5V		49	64	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	ID=1A, VGS=2.5V		68	95	mΩ	
	R _{DS} (on)3	ID=0.5A, VGS=1.8V		99	149	mΩ	
Input Capacitance	Ciss			260		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		65		pF	
Reverse Transfer Capacitance	Crss			50		pF	
Turn-ON Delay Time	t _d (on)			6.2		ns	
Rise Time	tr			19		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		30		ns	
Fall Time	tf			28		ns	
Total Gate Charge	Qg			2.8		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =3.5A		0.6		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		0.9		nC	
Diode Forward Voltage	V _{SD}	IS=3.5A, VGS=0V		0.85	1.2	V	

Switching Time Test Circuit

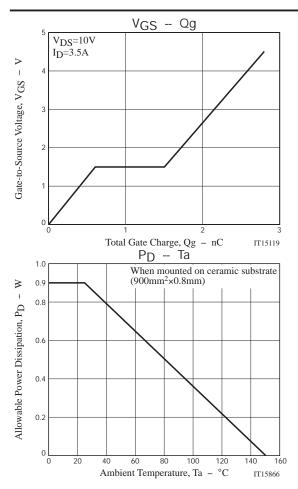


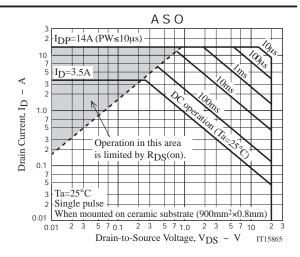
Ordering Information

Device Package		Shipping	memo		
MCH3479-TL-H	MCPH3	3,000pcs./reel	Pb Free and Halogen Free		



MCH3479





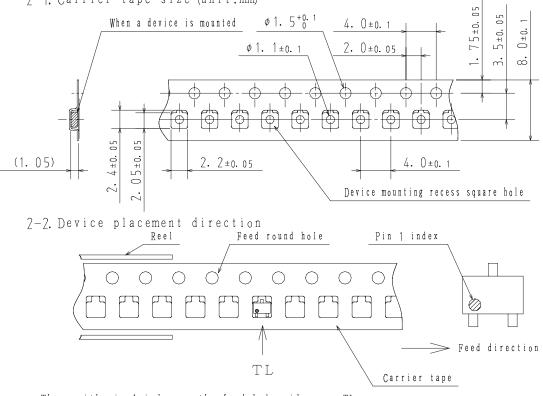
Taping Specification MCH3479-TL-H

1. Packing Format

Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing format			
	Туре	Reel	Inner box	Outer box	Inr	ner BO	X (C-1)	Outer BOX (A-7)
MCPH3	МСРН3	3,000	15,000	90,000	5 ree	ls contai	n e d	6 inner boxes contained
	_				Dimensions:mm (external)		n (externa	1) Dimensions:mm (external)
					18	3×72	×185	440×195×210
Packing met	hod Type LOT			TYPE 000C	nit:m 59	im)	It i The	<u>ver box label</u> s a label at the time of factory shipment form of a label may change in physical ribution process. <u>108</u> <u>TYPE CODE </u>
	Quan Orig	tity		U IIIIII IIIIII O GTY O, OC U IIIIIII IIIIII SPECIAL U IIIIIIIIIIIIII * Z O 7 Z 2 SSEMBLY:***** (C (1)) O ⁽¹⁾ lea ⁽¹⁾ lea 0 0 5 3 1 0	D FREE #	8 8 0	GTY 0,000 PCS (I) LOT PACKAGE (I) SPECIAL (IIII) (IIIII) ASSEMBLY:***** (DIFFUSION:*****) (I)
	∖ Reel la	ıbel		ie LEAD Fl eatment				that the surface free.
				Label			A Phase	
				LEAD FRE	-		Phase 3	
				LEAD FRI	ヒヒ 4	JEITA	Phase 3	

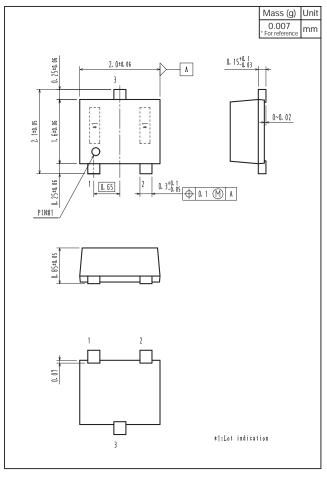
2. Taping configuration

2-1. Carrier tape size (unit:mm)

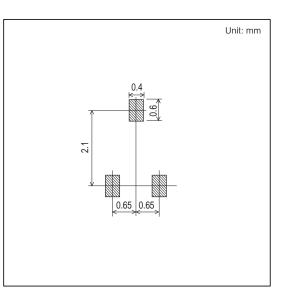


Those with pin 1 index on the feed hole side $\cdots \cdots TL$

Outline Drawing MCH3479-TL-H



Land Pattern Example



Note on usage : Since the MCH3479 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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